

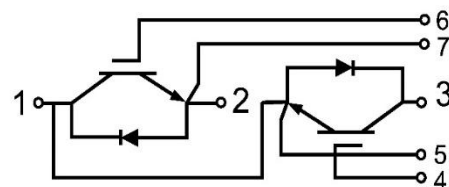
GT200HF170T2VH

Circuit Diagram

IGBT Module

Features:

- $V_{CES}=1700V$ $I_C=200A$ Trench & Field Stop IGBT Module
- Short Circuit Capability
- Low Switching Loss
- 100% RBSOA Tested($2 \times I_C$)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Industrial Inverters
- Motor Drives
- UPS Systems

Type	Package	Marking
GT200HF170T2VH	T2V	GT200HF170T2VH

IGBT, Inverter

Maximum Rated Values ($T_C=25^\circ C$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1700	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current, Limited by T_{Jmax}	$T_C=90^\circ C$	200	A
		$T_C=25^\circ C$	400	A
I_{CM}	Peak Collector Current Repetitive	t_p limited by T_{Jmax}	400	A
P_D	Maximum Power Dissipation (IGBT)	$T_C=25^\circ C, T_{Jmax}=175^\circ C$	1700	W

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Electrical Characteristics of IGBT ($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Static Characteristics

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=8\text{mA}$, $V_{CE}=V_{GE}$	5.0	6.0	7.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=200\text{A}$, $V_{GE}=15\text{V}$	$T_J=25^{\circ}\text{C}$	1.78	2.30	V
			$T_J=125^{\circ}\text{C}$	2.27		V
			$T_J=150^{\circ}\text{C}$	2.36		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}$, $V_{CE}=1700\text{V}$, $T_J=25^{\circ}\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=20\text{V}$, $V_{CE}=0\text{V}$, $T_J=25^{\circ}\text{C}$			400	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=100\text{kHz}$		18.90		nF
C_{oes}	Output Capacitance			1.67		nF
C_{res}	Reverse Transfer Capacitance			0.24		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=900V, I_c=200A,$ $R_{Gon}=1\Omega, V_{GE}=+15V/-15V,$ Inductive Load	$T_J=25^{\circ}C$		227		ns
			$T_J=125^{\circ}C$		230		
			$T_J=150^{\circ}C$		240		
t_r	Rise Time		$T_J=25^{\circ}C$		61		ns
			$T_J=125^{\circ}C$		70		
			$T_J=150^{\circ}C$		80		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^{\circ}C$		523		ns
			$T_J=125^{\circ}C$		600		
			$T_J=150^{\circ}C$		630		
t_f	Fall Time	$T_J=25^{\circ}C$		321		ns	
		$T_J=125^{\circ}C$		390			
		$T_J=150^{\circ}C$		420			
E_{on}	Turn-on Switching Loss	$V_{CC}=900V, I_c=200A,$ $R_{Gon}=1\Omega, V_{GE}=+15V/-15V,$ $di/dt=6000A/\mu s(T_J=150^{\circ}C)$ Inductive Load	$T_J=25^{\circ}C$		60		mJ
		$T_J=125^{\circ}C$		70			
		$T_J=150^{\circ}C$		84			

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E _{off}	Turn-off Switching Loss	V _{CC} =900V, I _C =200A, R _{Goff} =1Ω, V _{GE} =+15V/-15V, du/dt=6000V/μs(T _J =150°C) Inductive Load	T _J =25°C		42		mJ
			T _J =125°C		47		
			T _J =150°C		58		
Q _g	Total Gate Charge	V _{CE} =900V, V _{GE} =±15V, I _C =200A	T _J =25°C		1.58		μC
R _{G (int)}	Internal Gate Resistance		T _J =25°C		2.5		Ω
T _{SC}	V _{CC} =1000V, V _{GE} =±15V, T _J =150°C ^{note1}					10	μs
R _{θJC}	IGBT Thermal Resistance: Junction-to-Case (per IGBT)					0.087	°C/W
R _{θCS}	IGBT Thermal Resistance: Case-to-Sink (per IGBT) (per IGBT, λ _{grease} = 1 W/(m · K))				0.043		°C/W

note1: Short circuit withstand time cannot exceed 10μs under specified condition

Diode, Inverter

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	T _J =25°C	1700	V
I _F	Diode Continuous Forward Current		200	A
I _{FM}	Diode Maximum Forward Current	t _p =1ms	400	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions		Min.	Typ.	Max.	Units
V _{FM}	Forward Voltage	I _F =200A	T _J =25°C		1.92	2.40	V
			T _J =125°C		2.21		
			T _J =150°C		2.22		
t _{rr}	Reverse Recovery Time	I _F =200A, -diF/dt=6100A/μs(T _J =150°C), V _{CC} =900V, V _{GE} =-15V	T _J =25°C		556		ns
			T _J =125°C		880		
			T _J =150°C		900		
I _{rr}	Peak Reverse Recovery Current		T _J =25°C		180		A
			T _J =125°C		186		
			T _J =150°C		186		
Q _{rr}	Reverse Recovery Charge		T _J =25°C		40		μC
			T _J =125°C		62		
			T _J =150°C		65		

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E _{rec}	Reverse Recovery Energy	I _F =200A, -diF/dt=6100A/μs(T _J =150°C), V _{CC} =900V, V _{GE} =-15V	T _J =25°C		23		mJ
			T _J =125°C		32		
			T _J =150°C		34		
R _{θJC}	Diode Thermal Resistance: Junction-to-Case (per Diode)					0.134	°C/W
R _{θCS}	Diode Thermal Resistance: Case-to-Sink (per Diode, λ _{grease} = 1 W/(m • K))				0.066		°C/W

Module

Symbol	Description	Conditions	Min.	Typ.	Max.	Units
V _{iso}	Isolation Voltage (All Terminals Shorted)	f=50Hz, 1minute	3400			V
T _J	Maximum Junction Temperature		-40		175	°C
T _{JOP}	Maximum Operating Junction Temperature Range ^{note2}		-40		175	°C
T _{stg}	Storage Temperature		-40		125	°C
CTI	Comparative Tracking Index		200			
T	Power Terminals Screw:M6		3		5	N·m
T	Mounting Screw:M6		3		6	N·m
G	Weight			300		g

note2: T_{JOP}> 150°C is only allowed for operation at overload conditions.

Ordering Information Table

Device code

G	T	200	HF	170	T2V	H
①	②	③	④	⑤	⑥	⑦

- ① - IGBT Module
- ② - Trench, Low Switching Losses IGBT
- ③ - Rated Current (200=200A)
- ④ - Circuit Configuration : HF(Half Bridge)
- ⑤ - Rated Voltage (170=1700V)
- ⑥ - Package Type
- ⑦ - Test Level (Pass the Important Reliability Test-Industrial Grade)

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IGBT Module Datasheet



Characteristic diagram

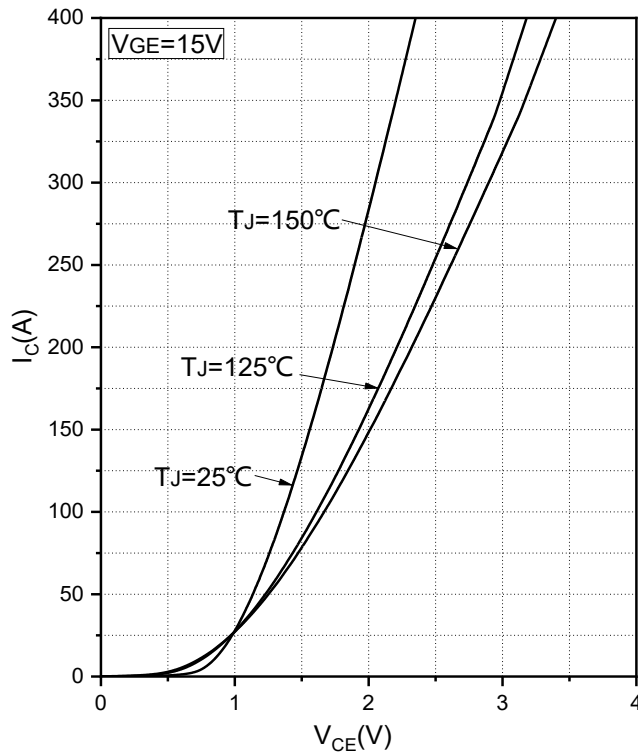


Fig.1 Typical Saturation Voltage Characteristics

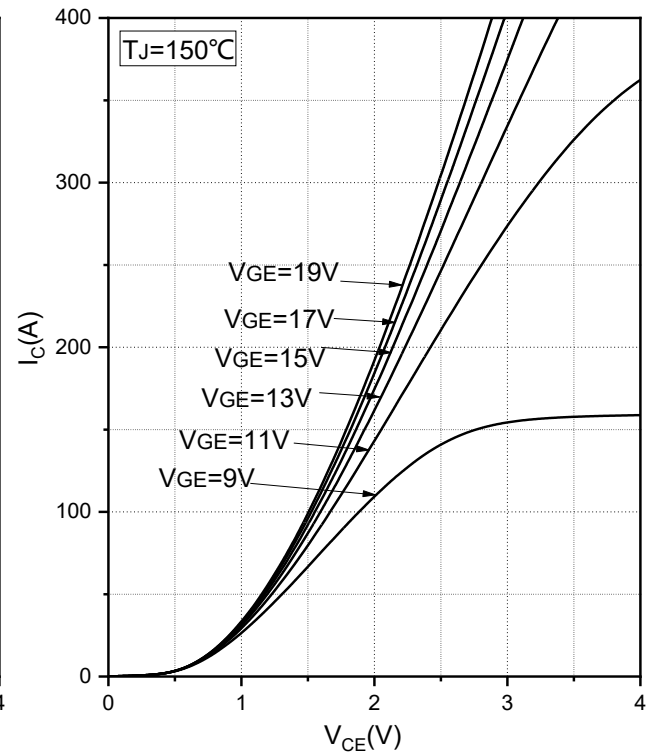


Fig.2 Typical Output Characteristics

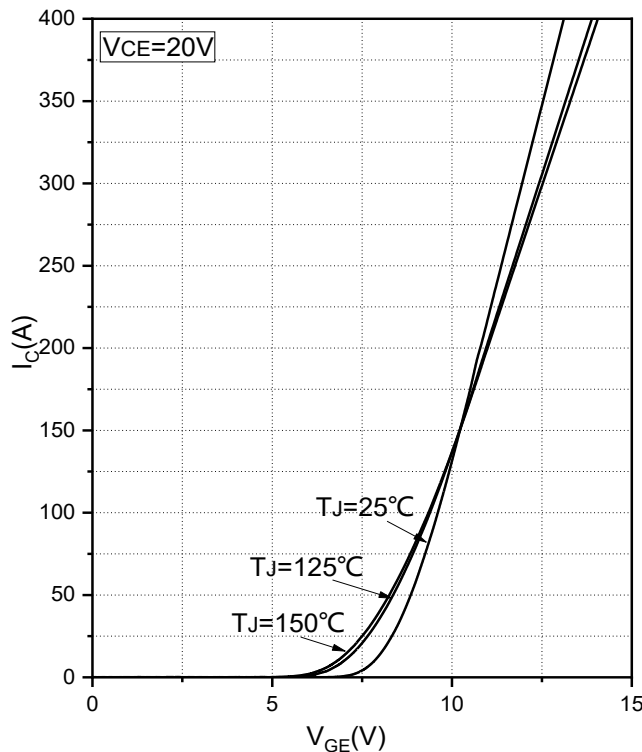


Fig.3 Transfer Characteristic

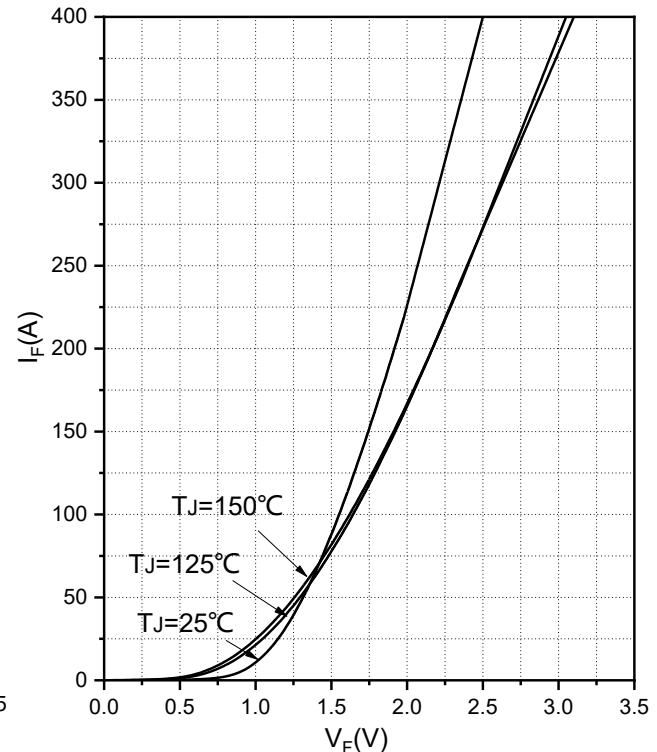


Fig.4 Forward Characteristics of Diode

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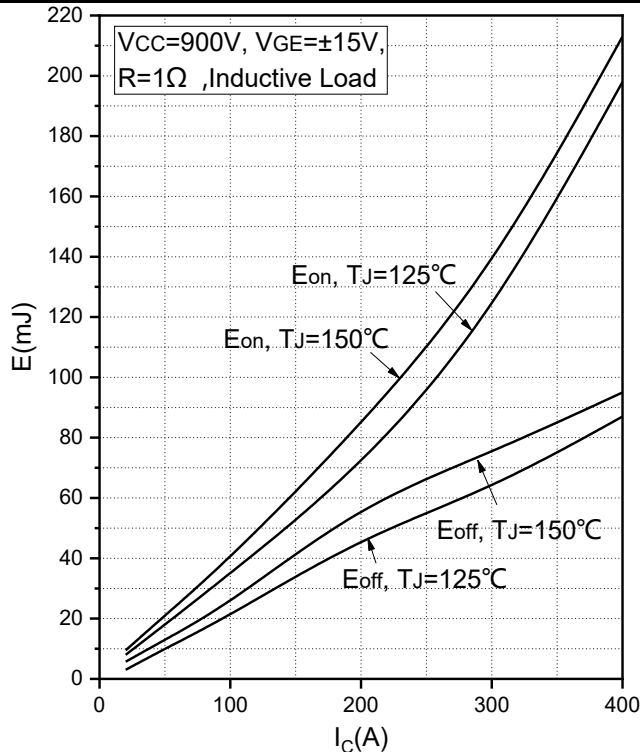


Fig.5 Typical Switching Loss IGBT vs. Collector Current

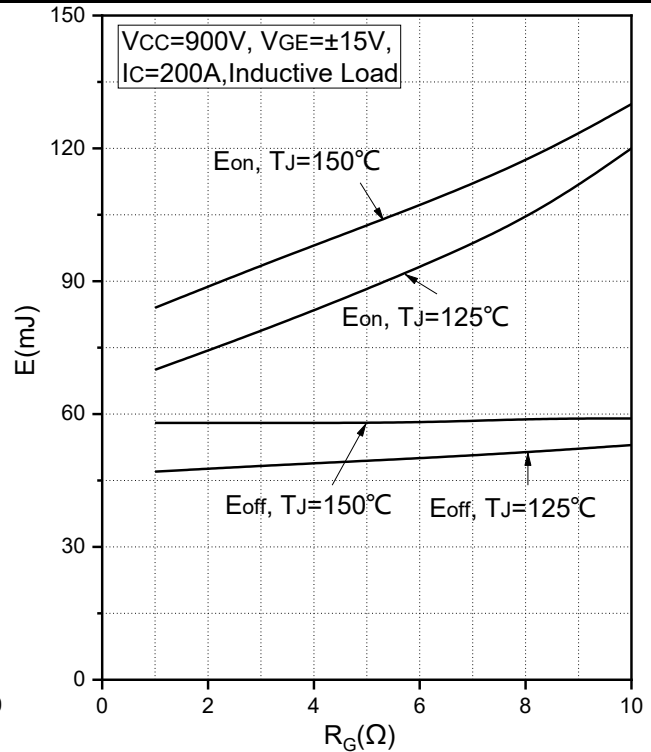


Fig.6 Typical Switching Loss IGBT vs. Gate Resistance

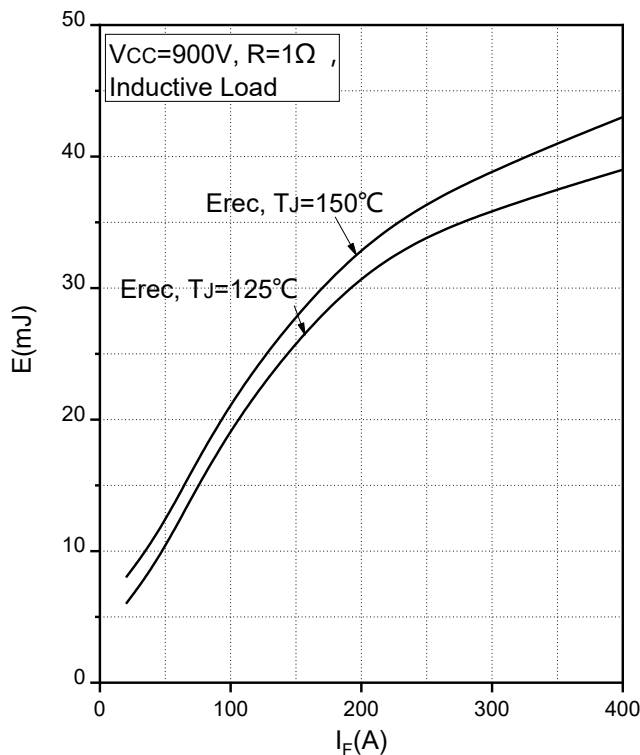


Fig.7 Typical Switching Loss Diode vs. Forward Current

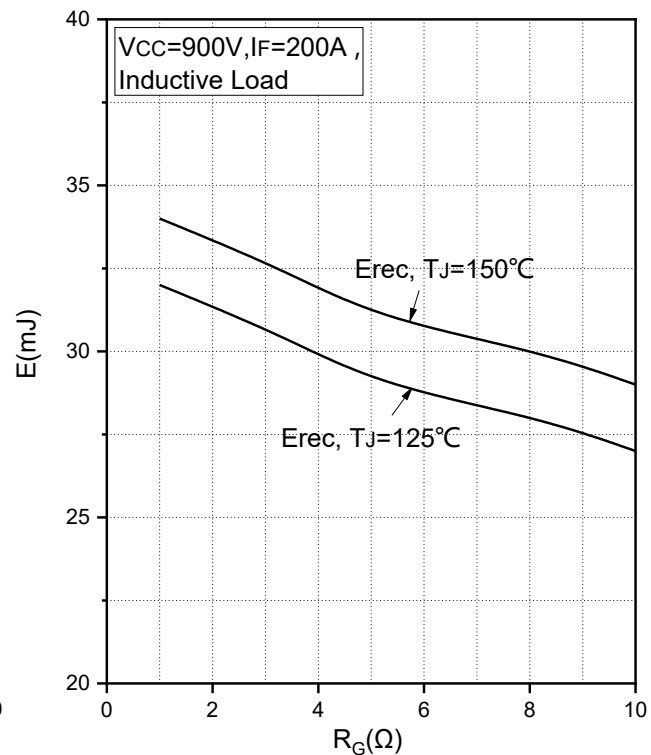


Fig.8 Typical Switching Loss Diode vs. Gate Resistance

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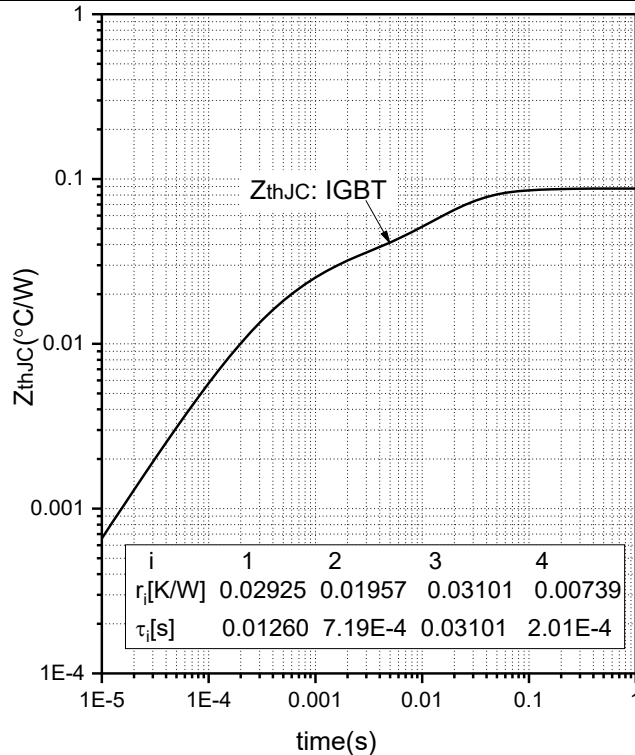


Fig.9 Transient Thermal Impedance (IGBT)

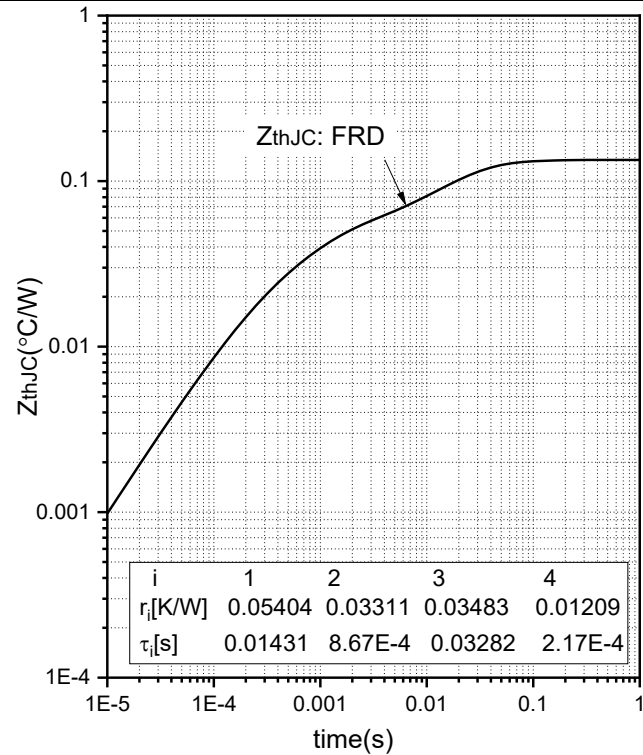


Fig.10 Transient Thermal Impedance (Diode)

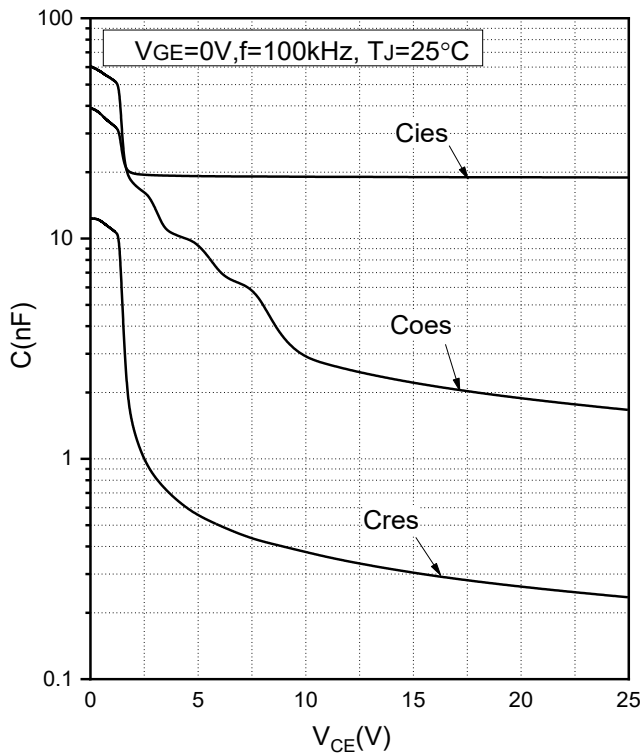


Fig.11 Capacitance Characteristics

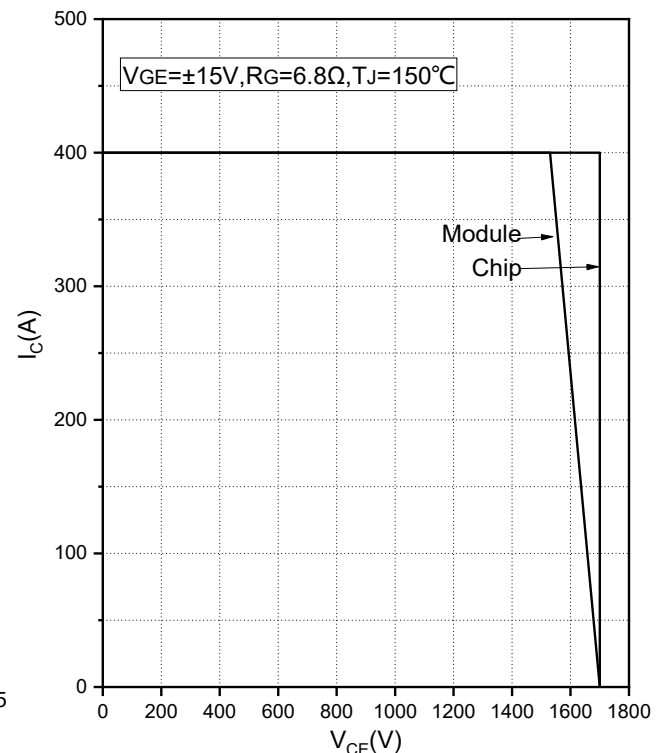


Fig.12 Reverse Bias Safe Operation Area (RBSOA)

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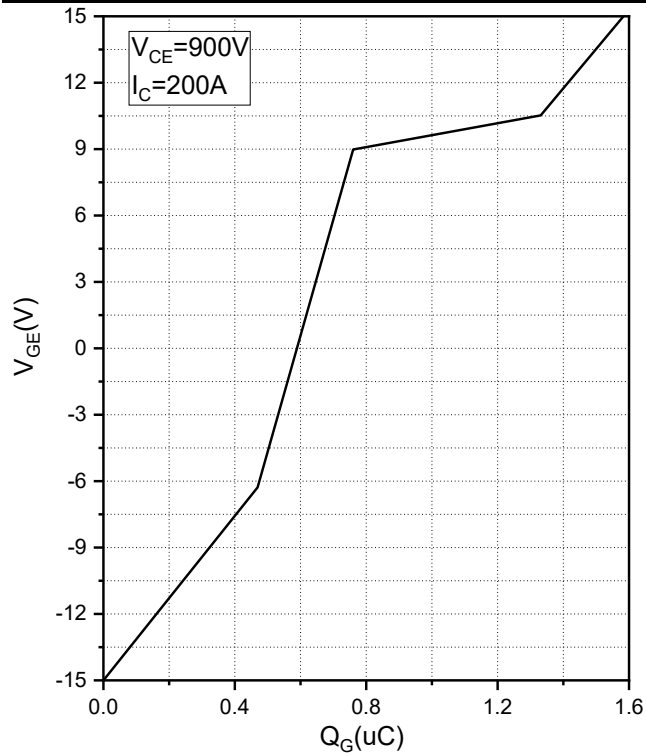


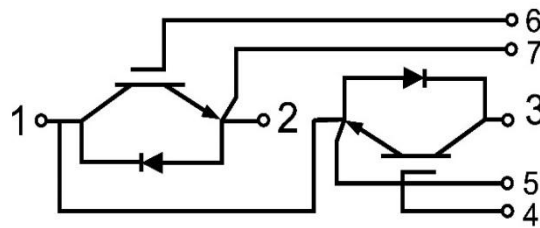
Fig.13 Gate Charge Characteristics

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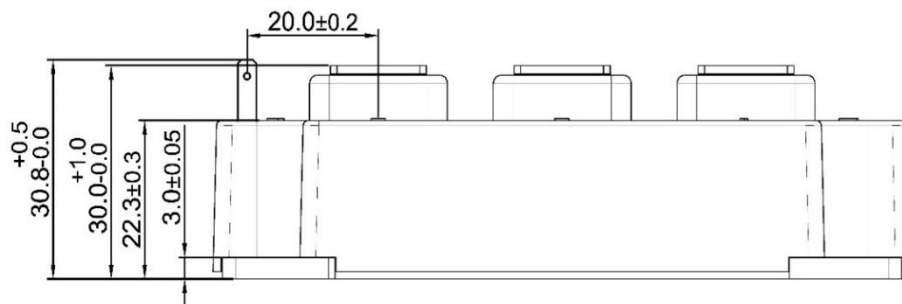
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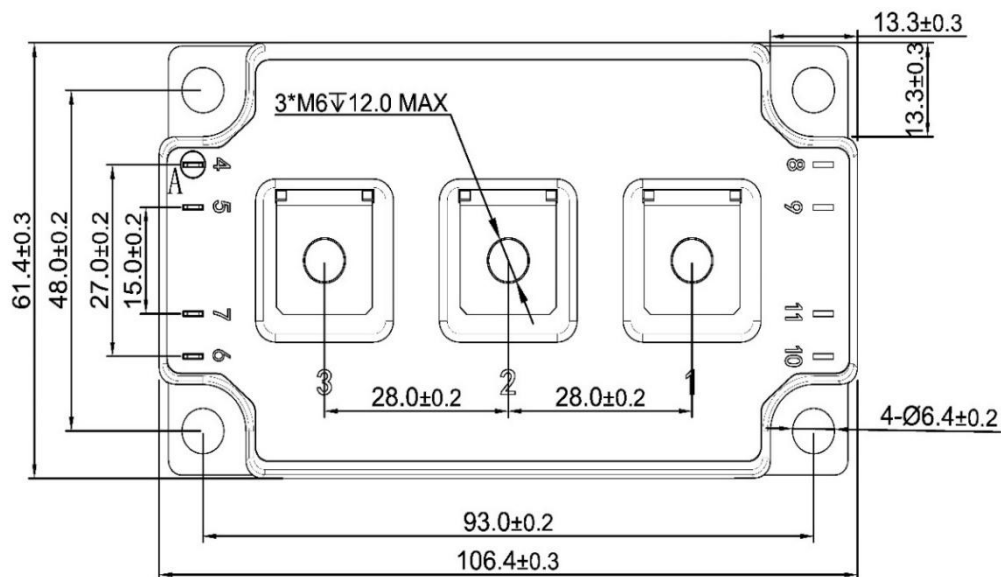
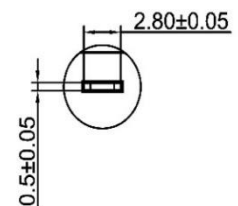
Internal Circuit:



Package Outline (Unit: mm):



View A
scale 3:1



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IGBT Module Datasheet



Revision	Notes
01	Initial Release
02	Engineering Sample Datasheet

Announcement

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